

-	30	((427/58).CCLS.) and (MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:07
-	0	(((427/58).CCLS.) and (MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical))) and (((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((planari\$7 or conformal) near (layer or film))) and (resist or photoresist) and (DOF or (depth near2 focus)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:07
-	0	(((427/58).CCLS.) and (MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical))) and (((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((planari\$7 or conformal) near (layer or film))) and (layout))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:07
-	1440	(438/48-52).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:07
-	354	(MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((438/48-52).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:08
-	4	((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((438/48-52).CCLS.)) and (((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((planari\$7 or conformal) near (layer or film))) and (resist or photoresist) and (DOF or (depth near2 focus)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:08
-	1163	(716/19-21).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:26
-	33	(MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((716/19-21).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:27
-	0	(((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((planari\$7 or conformal) near (layer or film))) and (resist or photoresist) and (DOF or (depth near2 focus))) and ((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((716/19-21).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:27

-	0	(((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical))) and ((planari\$7 or conformal) near (layer or film))) and (layout)) and ((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((716/19-21).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:28
-	105	((716/19-21).CCLS.) and (DOF or (depth near2 focus))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:28
-	4	(((716/19-21).CCLS.) and (DOF or (depth near2 focus))) and ((planari\$7 or conformal) near (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:37
-	4	(((716/19-21).CCLS.) and (DOF or (depth near2 focus))) and ((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((716/19-21).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:33
-	459257	resist or photoresist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:33
-	3309938	Topology or topography or height or level	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:35
-	2815	(DOF or (depth near2 focus)) and (NA or (numerical near2 aperture)) and (wavelength or lambda)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:37
-	48033	((planari\$7 or conformal or fill\$4) near (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:38
-	460	((DOF or (depth near2 focus)) and (NA or (numerical near2 aperture)) and (wavelength or lambda)) and layout	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:38
-	43	(resist or photoresist) and (Topology or topography or height or level) and (((planari\$7 or conformal or fill\$4) near (layer or film))) and (((DOF or (depth near2 focus)) and (NA or (numerical near2 aperture)) and (wavelength or lambda)) and layout)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:39

L Number	Hits	Search Text	DB	Time stamp
-	1	09/854813	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 09:49
-	39874	MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 10:57
-	47	((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((planari\$7 or conformal) near (layer or film))) and (resist or photoresist) and (DOF or (depth near2 focus))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:33
-	85	((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((planari\$7 or conformal) near (layer or film))) and (layout)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 09:59
-	483	(MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((planari\$7 or conformal) near (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:29
-	316	430.clas. and (MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 10:59
-	3548	(430/322-324).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:00
-	75	(MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((430/322-324).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:00
-	0	((((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((planari\$7 or conformal) near (layer or film))) and (resist or photoresist) and (DOF or (depth near2 focus))) and ((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((430/322-324).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:00

-	0	(((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((planari\$7 or conformal) near (layer or film))) and (layout)) and ((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((430/322-324).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:00
-	2264	(257/415-420).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:01
-	216	(MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((257/415-420).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:01
-	3	(((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((planari\$7 or conformal) near (layer or film))) and (resist or photoresist) and (DOF or (depth near2 focus))) and ((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((257/415-420).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:01
-	2	(((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((planari\$7 or conformal) near (layer or film))) and (layout)) and ((MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((257/415-420).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:04
-	570	(264/401).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:04
-	11	(MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical)) and ((264/401).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:05
-	356	427.clas. and (MEMS or (Micro\$2electro\$2mechanical) or (micro near2 mechanical))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:06
-	1506	(427/58).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 11:06